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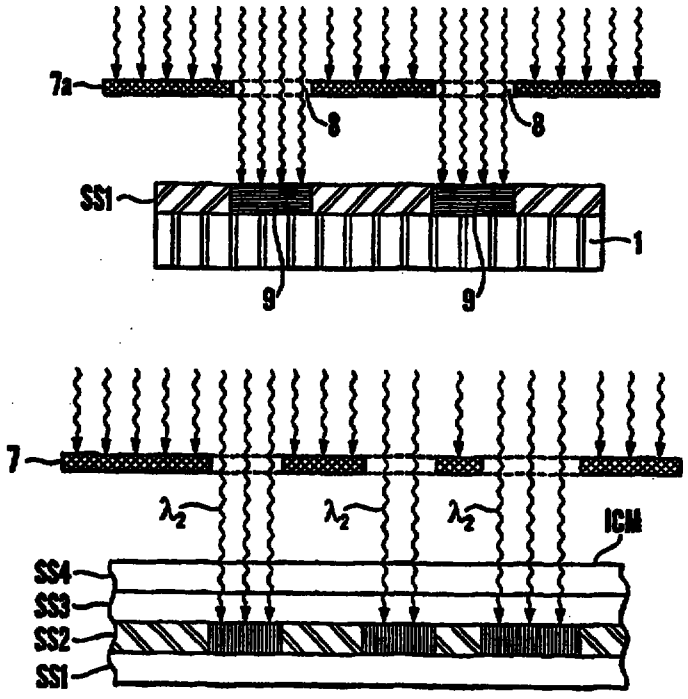
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(54) Title: A METHOD FOR GENERATION OF ELECTRICAL CONDUCTING OR SEMICONDUCTING STRUCTURES IN THREE DIMENSIONS AND METHODS FOR ERASURE OF THE SAME STRUCTURES

(57) Abstract

In a method for generating electrical conducting or semiconducting structures in three dimensions in a matrix which comprises two or more materials in spatially separate material structures, each material structure is irradiated with a radiation of a given intensity and/or frequency characteristic adapted to the material's response thereto, the radiation being modulated spatially according to a determined protocol which represents a predetermined pattern of electrical conducting or semiconducting structures in the relevant material structure and in response to the irradiation two–dimensional electrical conducting or semiconducting structures with a predetermined pattern are generated in the material structure such that the matrix comprised by the material structures is provided with electrical conducting or semiconducting structures in three dimensions. In a method for erasing electrical conducting or semiconducting structures of this kind each material structure is irradiated in a corresponding manner as in the generation of the structures, but such that the two–dimensional electrical conducting or semiconducting structures which are present in the material structure in response to the radiation are erased and the material in the structure in its entirety transfers to an electrical non–conducting state.



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